

IXTP75N10P-VB Datasheet

N-Channel 100-V (D-S) MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ (Ω)	I_D (A)
100	0.017 at $V_{GS} = 10$ V	70 ^a

FEATURES

- Trench Power MOSFET
- 175 °C Junction Temperature
- Low Thermal Resistance Package
- 100 % R_g Tested

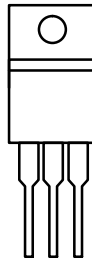


RoHS
COMPLIANT

APPLICATIONS

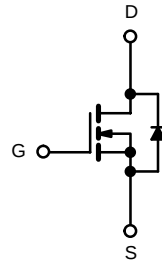
- Isolated DC/DC Converters

TO-220AB



G D S

Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_C = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 175$ °C)	I_D	70 ^a	A
		35 ^a	
Pulsed Drain Current	I_{DM}	145	
Avalanche Current	I_{AS}	31	
Single Pulse Avalanche Energy ^b	E_{AS}	60	mJ
Maximum Power Dissipation ^b	P_D	355 ^c	W
		3.35	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Limit	Unit
Junction-to-Ambient	R_{thJA}	40	°C/W
Junction-to-Case (Drain)	R_{thJC}	0.4	

Notes:

a. Package limited.

b. Duty cycle ≤ 1 %.

c. See SOA curve for voltage derating.

d. When Mounted on 1" square PCB (FR-4 material).

SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{DS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	100			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2		4	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^{\circ}\text{C}$			50	
		$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^{\circ}\text{C}$			250	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	120			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 30\text{ A}$		0.017		Ω
		$V_{GS} = 10\text{ V}, I_D = 30\text{ A}, T_J = 125\text{ }^{\circ}\text{C}$		0.023		
		$V_{GS} = 10\text{ V}, I_D = 30\text{ A}, T_J = 175\text{ }^{\circ}\text{C}$		0.037		
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 30\text{ A}$	25			S
Dynamic ^b						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		1800		pF
Output Capacitance	C_{oss}			210		
Reverse Transfer Capacitance	C_{rss}			110		
Total Gate Charge ^c	Q_g	$V_{DS} = 100\text{ V}, V_{GS} = 10\text{ V}, I_D = 58\text{ A}$		90		nC
Gate-Source Charge ^c	Q_{gs}			23		
Gate-Drain Charge ^c	Q_{gd}			34		
Gate Resistance	R_g		0.5	1.3	3.1	Ω
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = 100\text{ V}, R_L = 1.5\text{ }\Omega$ $I_D \cong 58\text{ A}, V_{GEN} = 10\text{ V}, R_g = 2.5\text{ }\Omega$		24	35	ns
Rise Time ^c	t_r			220	330	
Turn-Off Delay Time ^c	$t_{d(off)}$			45	70	
Fall Time ^c	t_f			200	300	
Source-Drain Diode Ratings and Characteristics $T_C = 25\text{ }^{\circ}\text{C}^b$						
Continuous Current	I_S				70	A
Pulsed Current	I_{SM}			115		
Forward Voltage ^a	V_{SD}	$I_F = 58\text{ A}, V_{GS} = 0\text{ V}$		1.0	1.5	V
Reverse Recovery Time	t_{rr}	$I_F = 30\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		130	200	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			8	12	A
Reverse Recovery Charge	Q_{rr}			0.52	1.2	μC

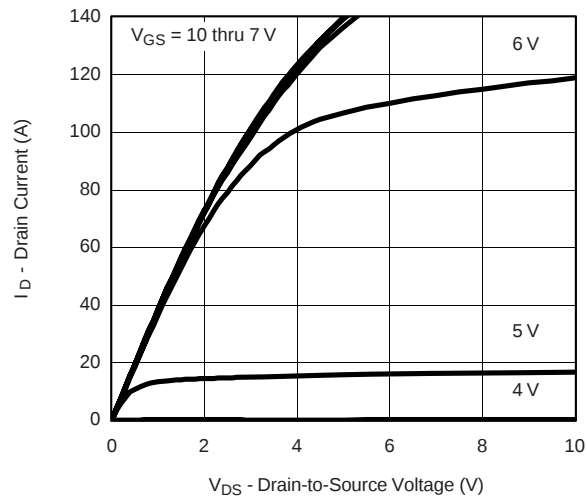
Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

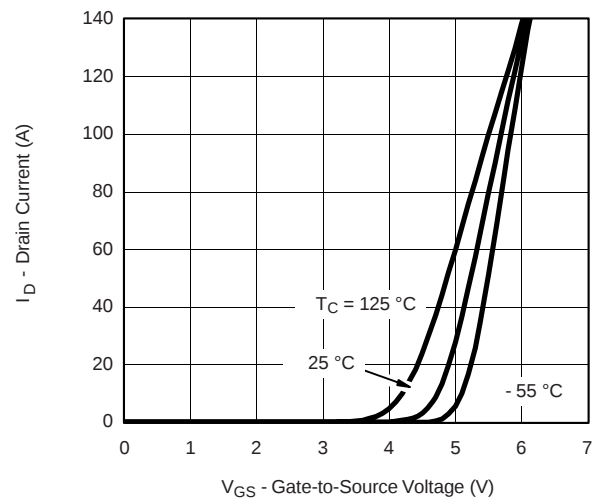
b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

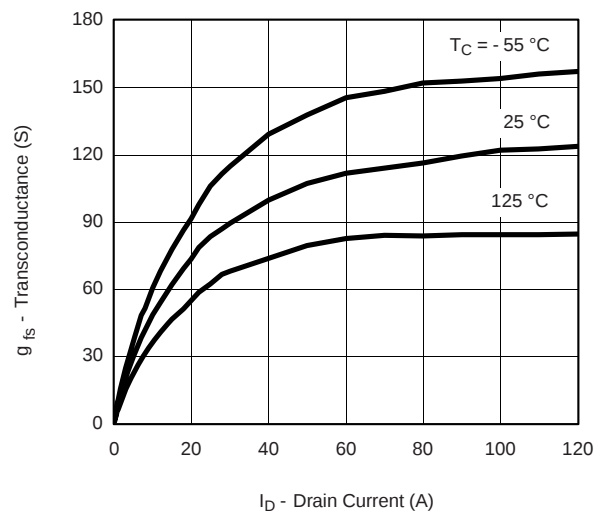
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


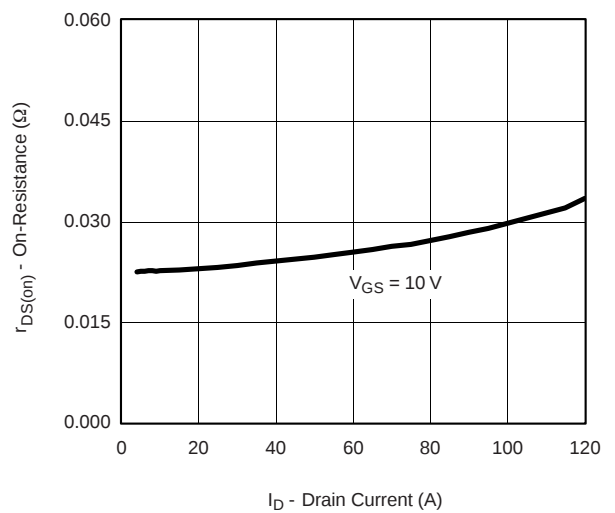
Output Characteristics



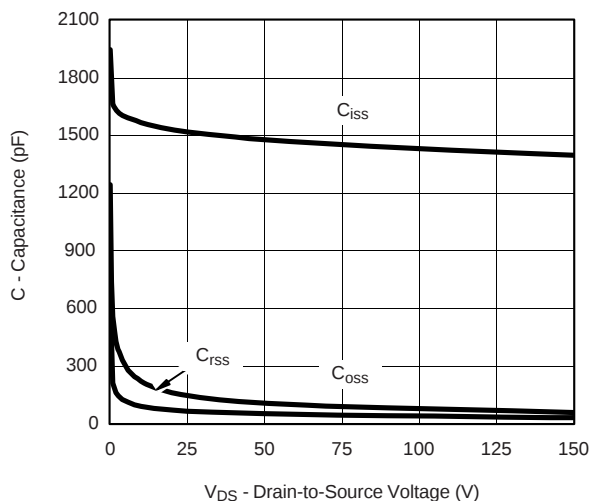
Transfer Characteristics



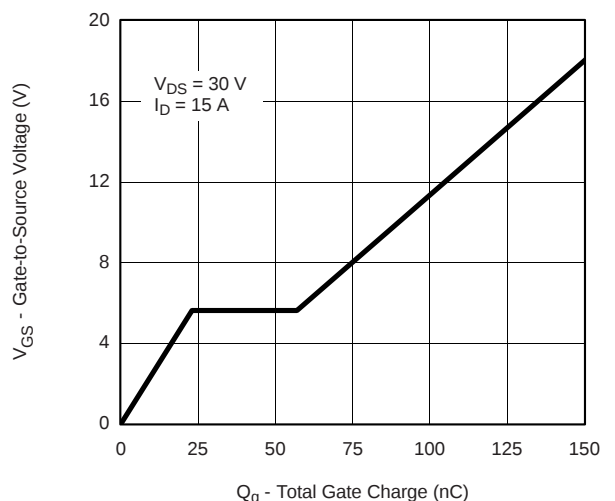
Transconductance



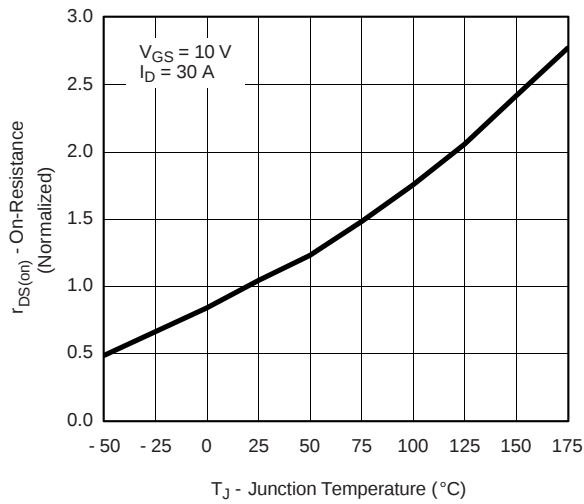
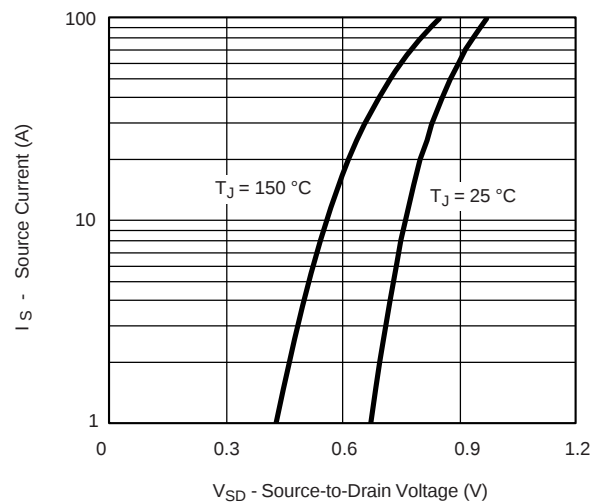
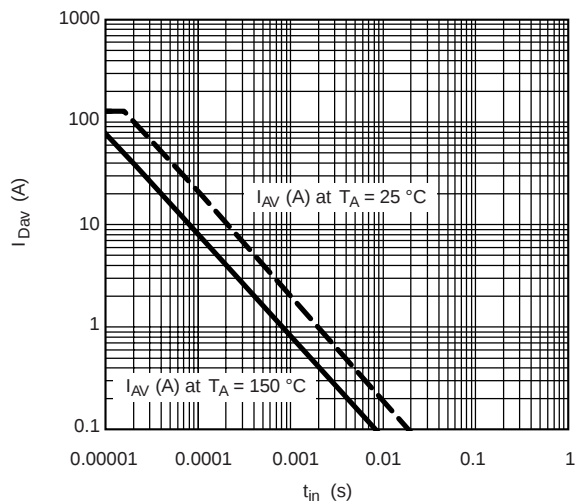
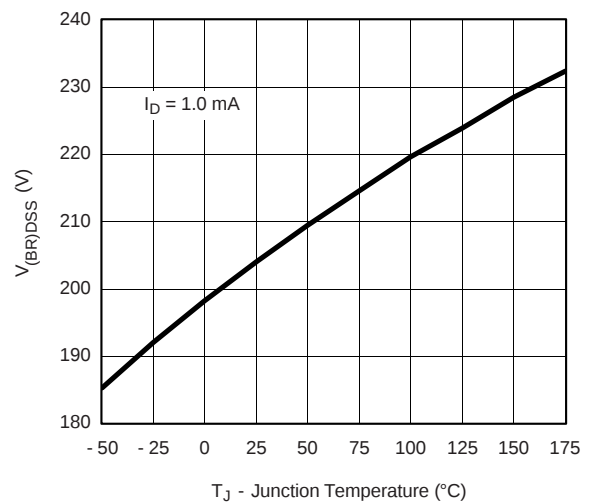
On-Resistance vs. Drain Current



Capacitance



Gate Charge

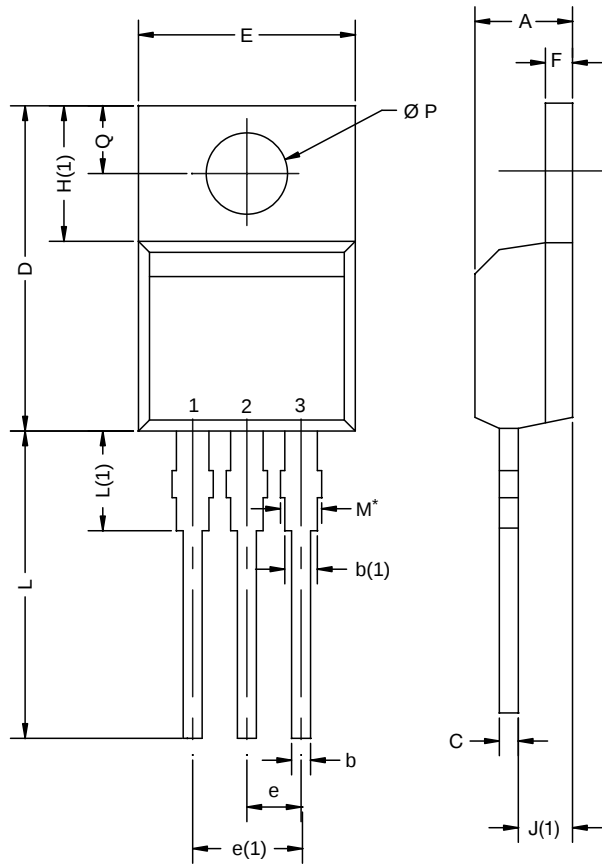
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

On-Resistance vs. Junction Temperature

Source-Drain Diode Forward Voltage

Avalanche Current vs. Time

Drain Source Breakdown vs. Junction Temperature

T_C - Ambient Temperature ($^{\circ}\text{C}$)	I_D - Drain Current (A)
0	65
25	65
50	60
75	55
100	45
125	35
150	25
175	0

Figure 10 is a log-log plot showing the Power Dissipation Characteristics (Drain Current I_D vs. Drain-to-Source Voltage V_{DS}) for a Single Pulse at $T_C = 25^\circ\text{C}$. The Y-axis represents I_D - Drain Current (A) on a logarithmic scale from 0.1 to 1000. The X-axis represents V_{DS} - Drain-to-Source Voltage (V) on a logarithmic scale from 0.1 to 1000. The plot includes curves for various pulse widths: 10 μs , 100 μs , 1 ms, 10 ms, 100 ms, and DC. A horizontal line at $I_D \approx 120\text{ A}$ is labeled $r_{DS(on)}$ Limited*.

* $V_{GS} >$ minimum V_{GS} at which $r_{DS(on)}$ is specified

Normalized Thermal Transient Impedance, Junction-to-Case

TO-220AB

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
Ø P	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118
ECN: X12-0208-Rev. N, 08-Oct-12				
DWG: 5471				

Notes

* M = 1.32 mm to 1.62 mm (dimension including protrusion)
 Heatsink hole for HVM

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